

L Number	Hits	Search Text	DB	Time stamp
-	213204	257/\$3.ccls. or 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2003/07/01 14:45
-	6	(257/\$3.ccls. or 438/\$3.ccls.) and insulat\$3 and radiat\$3 and (amorphous near2 silicon) and crystall\$7 and explosive	USPAT; EPO; JPO; DERWENT	2002/04/09 09:46
-	1	(257/\$3.ccls. or 438/\$3.ccls.) and (xcr or (explosive adj recrystallization)) and irradiat\$3 and dopant and gate	USPAT; EPO; JPO; DERWENT	2002/04/09 09:58
-	103	(257/\$3.ccls. or 438/\$3.ccls.) and recrystallization and irradiat\$3 and dopant and gate	USPAT; EPO; JPO; DERWENT	2002/04/09 09:59
-	85	((257/\$3.ccls. or 438/\$3.ccls.) and recrystallization and irradiat\$3 and dopant and gate) and (amorphous adj silicon)	USPAT; EPO; JPO; DERWENT	2002/04/09 15:19
-	3	mosfet same (laser or irradiate) same amorphous same (dopant or dope)	USPAT; EPO; JPO; DERWENT	2002/04/09 16:11
-	111	(laser or irradiate) same (amorphous adj silicon) same (dopant or dope)	USPAT; EPO; JPO; DERWENT	2002/04/10 16:52
-	10	((laser or irradiate) same (amorphous adj silicon) same (dopant or dope)) same (insulat\$4 adj layer)	USPAT; EPO; JPO; DERWENT	2002/04/09 16:14
-	241	mosfet with laser	USPAT; EPO; JPO; DERWENT	2002/04/09 17:50
-	2	(mosfet with laser) same (amorphous adj silicon)	USPAT; EPO; JPO; DERWENT	2002/04/09 17:52
-	12	(mosfet with laser) same (dope dopant doped)	USPAT; EPO; JPO; DERWENT	2002/04/09 18:06
-	42	(mosfet with laser) and ((dope dopant doped) with gate)	USPAT; EPO; JPO; DERWENT	2002/04/09 18:07
-	12557	(mosfet or fet or mos) same dop\$3 same gate	USPAT; EPO; JPO; DERWENT	2002/04/10 17:18
-	158	((mosfet or fet or mos) same dop\$3 same gate) same (laser or irradiation)	USPAT; EPO; JPO; DERWENT	2002/04/10 11:07
-	4	"5966605"	USPAT; EPO; JPO; DERWENT	2002/04/10 11:07
-	54793	gate with silicon	USPAT; EPO; JPO; DERWENT	2002/04/10 14:12
-	6957	((mosfet or fet or mos) same dop\$3 same gate) and (gate with silicon)	USPAT; EPO; JPO; DERWENT	2002/04/10 14:12
-	15744	gate near2 silicon	USPAT; EPO; JPO; DERWENT	2002/04/10 14:12
-	2731	((mosfet or fet or mos) same dop\$3 same gate) and (gate near2 silicon)	USPAT; EPO; JPO; DERWENT	2002/04/10 14:12
-	234	((mosfet or fet or mos) same dop\$3 same gate) and (gate near2 silicon)) and (laser or irradiate)	USPAT; EPO; JPO; DERWENT	2002/04/10 14:15
-	110	((mosfet or fet or mos) same dop\$3 same gate) and (gate near2 silicon)) and (laser or irradiate)) and amorphous and (recrystallize or polycrystalline or crystalline)	USPAT; EPO; JPO; DERWENT	2002/04/10 16:15

-	13	"5937325"	USPAT; EPO; JPO; DERWENT	2002/04/10 16:19
-	8	"6013928"	USPAT; EPO; JPO; DERWENT	2002/04/10 16:20
-	34	(laser or irradiate) same (amorphous adj silicon) same ((dopant or dope) and (sputter or deposition or evaporation))	USPAT; EPO; JPO; DERWENT	2002/04/10 16:53
-	3488	(mosfet or fet or mos) same dop\$3 same gate same (sputter or evaporat\$3 or deposit\$3)	USPAT; EPO; JPO; DERWENT	2002/04/10 17:20
-	3958	((mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or deposit\$3 or evaporat\$3))	USPAT; EPO; JPO; DERWENT	2002/04/10 17:21
-	137	((mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3))	USPAT; EPO; JPO; DERWENT	2002/04/10 17:21
-	41	((mosfet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter or evaporat\$3))	USPAT; EPO; JPO; DERWENT	2002/04/10 17:25
-	75	((mosfet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3))	USPAT; EPO; JPO; DERWENT	2002/04/10 17:32
-	320	(dop\$3 with (sputter\$3 or evaporat\$3) with silicon) and (mos or fet or mosfet)	USPAT; EPO; JPO; DERWENT	2002/04/10 17:46
-	35	(dop\$3 with (sputter\$3 or evaporat\$3) with silicon) same (mos or fet or mosfet)	USPAT; EPO; JPO; DERWENT	2002/04/10 17:35
-	28	(dop\$3 with (sputter\$3 or evaporat\$3) with silicon) same laser	USPAT; EPO; JPO; DERWENT	2002/04/10 17:51
-	190	(dop\$3 with (sputter\$3 or evaporat\$3)) same laser	USPAT; EPO; JPO; DERWENT	2002/04/10 18:02
-	2	"6165875"	USPAT; EPO; JPO; DERWENT	2002/04/10 18:02
-	2848	gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)	USPAT; EPO; JPO; DERWENT	2002/04/11 16:14
-	331	(gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) ) and laser	USPAT; EPO; JPO; DERWENT	2002/04/11 16:20
-	89	(gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) ) and laser and mosfet	USPAT; EPO; JPO; DERWENT	2002/04/11 16:20
-	4	"6077758"	USPAT; JPO; DERWENT	2002/04/11 17:34
-	11867	(boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)	USPAT; EPO; JPO; DERWENT	2002/04/15 14:06
-	12	((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)) same dopant same laser	USPAT; EPO; JPO; DERWENT	2002/04/15 14:02
-	1098	((boron or indium or arsenic or phosphorus) near2 layer) with (sputter\$3 or CVD or evaporat\$3)	USPAT; EPO; JPO; DERWENT	2002/04/15 15:10
-	33	((boron or indium or arsenic or phosphorus) near2 layer) with (sputter\$3 or CVD or evaporat\$3)) same dopant	USPAT; EPO; JPO; DERWENT	2002/04/15 14:09
-	239	((boron or indium or arsenic or phosphorus) near2 layer) with (sputter\$3 or CVD or evaporat\$3) with surface	USPAT; EPO; JPO; DERWENT	2002/04/15 15:13
-	46	((boron or indium or arsenic or phosphorus) near2 layer) with (sputter\$3 or CVD or evaporat\$3) with surface) and laser	USPAT; EPO; JPO; DERWENT	2002/04/15 15:14

-	2	5966605.pn.	USPAT; EPO; JPO; DERWENT	2002/09/13 13:14
-	2	6365476.pn.	USPAT; EPO; JPO; DERWENT	2002/09/13 13:15
-	2	6274488.pn.	USPAT; EPO; JPO; DERWENT	2002/09/13 13:16
-	2	6077758.pn.	USPAT; EPO; JPO; DERWENT	2002/09/13 13:16
-	1175	radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5	USPAT; EPO; JPO; DERWENT	2002/12/08 12:17
-	34	radiat\$3 same amorphous same silicon same dop\$3 same crystalliz\$5	USPAT; EPO; JPO; DERWENT	2002/12/08 12:12
-	12	(radiat\$3 same amorphous same silicon same dop\$3 same crystalliz\$5) same gate	USPAT; EPO; JPO; DERWENT	2002/12/08 12:12
-	350	radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3)	USPAT; EPO; JPO; DERWENT	2002/12/08 12:22
-	315	(radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3)) and laser	USPAT; EPO; JPO; DERWENT	2002/12/08 12:20
-	181	((radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3)) and laser) and 438/\$3.ccls.	USPAT; EPO; JPO; DERWENT	2002/12/08 12:21
-	181	((((radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3)) and laser) and 438/\$3.ccls.) and @ad<20010829	USPAT; EPO; JPO; DERWENT	2002/12/08 12:21
-	33	radiat\$3 and amorphous and silicon and dop\$3 and crystalliz\$5 and (gate with dop\$3 with amorphous)	USPAT; EPO; JPO; DERWENT	2002/12/08 12:59
-	4	radiat\$3 and (crystalliz\$5 with gate with dop\$3 with amorphous)	USPAT; EPO; JPO; DERWENT	2002/12/08 13:04
-	2	radiat\$3 same amorphous same (crystalliz\$5 with gate with dop\$3)	USPAT; EPO; JPO; DERWENT	2002/12/08 13:08
-	11	radiat\$3 same amorphous same crystalliz\$5 same (gate with dop\$3)	USPAT; EPO; JPO; DERWENT	2002/12/08 13:30
-	28	anneal\$3 same crystalliz\$5 same (amorphous with gate with dop\$3)	USPAT; EPO; JPO; DERWENT	2002/12/08 15:51
-	3	("5872761"   "5994179"   "6054355").PN.	USPAT	2002/12/08 14:00
-	11	gate with height with "500" with (nanometer\$1 or nm)	USPAT; EPO; JPO; DERWENT	2002/12/08 15:55
-	62	gate with height with ("400" or "300" or "200" or "100") with (nanometer\$1 or nm)	USPAT; EPO; JPO; DERWENT	2002/12/08 15:56
-	2	6159782.pn.	USPAT; EPO; JPO; DERWENT	2003/06/03 14:19
-	144	xcr or (explosive adj \$2crystalliz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:59
-	0	(xcr or (explosive adj \$2crystalliz\$4)) and (laser same amorphous same (polycrystalline or polysilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:57

-	127	xcr and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:00
-	0	(xcr and @ad<20010829) and laser and amorphous and (polycrystalline or polysilicon) and (dopant or boron)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:58
-	138	xcr	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:58
-	0	(xcr and @ad<20010829) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:59
-	6	explosive adj \$2crystalliz\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:59
-	35	explosive adj \$2crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:59
-	16	(explosive adj \$2crystalliz\$5) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:42
-	15	((explosive adj \$2crystalliz\$5) and 438/\$3.ccls.) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:46
-	18	("4522845"   "4622735"   "4683645"   "4830971"   "4924294"   "4931353"   "5010032"   "5122479"   "5236865"   "5302538"   "5405806"   "5563100"   "5593923"   "5888888"   "6060392"   "6072222"   "6174774"   "6274488").PN.	USPAT	2003/06/30 16:02
-	10	("4151008"   "4456490"   "4617066"   "5756369"   "5897381"   "5908307"   "5923963"   "5989966"   "6153483"   "6188106").PN.	USPAT	2003/06/30 16:10
-	17	("4522845"   "4622735"   "4683645"   "4830971"   "4924294"   "4931353"   "5010032"   "5122479"   "5236865"   "5302538"   "5405806"   "5563100"   "5593923"   "5888888"   "6060392"   "6072222"   "6174774").PN.	USPAT	2003/06/30 16:23
-	646	laser same gate same dop\$3 same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:40
-	277	(laser same gate same dop\$3 same silicon) same amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:41
-	80	((laser same gate same dop\$3 same silicon) same amorphous) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:41
-	74	((((laser same gate same dop\$3 same silicon) same amorphous) same temperature) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:51
-	41	(((((laser same gate same dop\$3 same silicon) same amorphous) same temperature) and @ad<20010829) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:43

-	169	melting with temperature with amorphous with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT USPAT	2003/06/30 17:11
-	7	("5770486"   "5891766"   "5937325"   "5966605"   "5998272"   "6225176"   "6297115").PN.	USPAT	2003/06/30 17:29
-	3	laser same silicon same amorphous same wavelength same (pulse adj width) same (irradiance or fluence) same (repetition adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:45
-	19	laser same wavelength same (pulse adj width) same (irradiance or fluence) same (repetition adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:50
-	12	(laser same wavelength same (pulse adj width) same (irradiance or fluence) same (repetition adj rate)) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:20
-	10	((laser same wavelength same (pulse adj width) same (irradiance or fluence) same (repetition adj rate)) and @ad<20010829) not ultratech	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:46
-	293	laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:50
-	0	(((((laser same gate same dop\$3 same silicon) same amorphous) same temperature) and @ad<20010829) and (laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:51
-	1	(laser same gate same dop\$3 same silicon) and (laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:52
-	1	(melting with temperature with amorphous with silicon) and (laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:52
-	7	(laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate)) and (dopant or impurity) and amorphous and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:18
-	1416	diffus\$3 same amorphous same dop\$3 same silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:19
-	83	(diffus\$3 same amorphous same dop\$3 same silicon) same laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:19
-	1	(laser and wavelength and (pulse adj width) and (irradiance or fluence) and (repetition adj rate)) and ((diffus\$3 same amorphous same dop\$3 same silicon) same laser)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:20
-	72	((diffus\$3 same amorphous same dop\$3 same silicon) same laser) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:21
-	31	((diffus\$3 same amorphous same dop\$3 same silicon) same laser) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 18:21
-	28	(((((diffus\$3 same amorphous same dop\$3 same silicon) same laser) same gate) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 19:18

-	1	(dopant adj layer) with top with (amorphous adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 19:19
-	307	laser with (amorphous adj silicon) with (dop\$3 or impurity)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 19:20
-	70	(laser with (amorphous adj silicon) with (dop\$3 or impurity)) with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 19:20
-	13	((laser with (amorphous adj silicon) with (dop\$3 or impurity)) with gate) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 19:21
-	2	5908307.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:08
-	4	wavelength same (temporal adj pulse adj width) same (irradiance or fluence)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:10
-	10	(wavelength same (pulse adj width) same (irradiance or fluence)) and (melt\$3 with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:10
-	129	wavelength same (pulse adj width) same (irradiance or fluence)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/01 15:14